



BUK763R4-30B

N-channel TrenchMOS standard level FET

Rev. 2 — 21 April 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

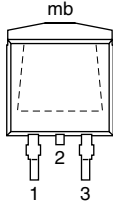
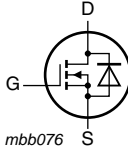
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	-	30	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1 ; see Figure 4	[1]	-	75	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	255	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; see Figure 12 ; see Figure 13	-	2.9	3.4	mΩ
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$; $V_{sup} \leq 30\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped	-	-	1.3	J

[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT404 (D2PAK)

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BUK763R4-30B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	30	V	
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	30	V	
V_{GS}	gate-source voltage		-20	20	V	
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; see Figure 4	[1]	-	75	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1	[1]	-	75	A
		$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; see Figure 4	[2][3]	-	198	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; see Figure 4	-	794	A	
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	255	W	
T_{stg}	storage temperature		-55	175	°C	
T_j	junction temperature		-55	175	°C	
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ °C}$	[2][3]	-	198	A
			[1]	-	75	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	794	A	
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$; $V_{sup} \leq 30\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; unclamped	-	1.3	J	
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	see Figure 3	[4][5][6] [7]	-	J	

[1] Continuous current is limited by package.

[2] Current is limited by power dissipation chip rating.

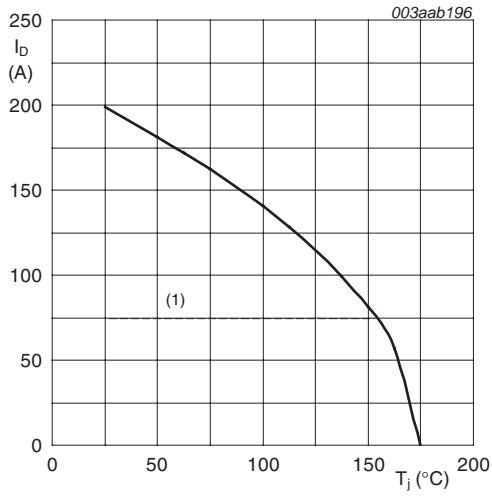
[3] Refer to document 9397 750 12572 for further information.

[4] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

[5] Single-shot avalanche rating limited by maximum junction temperature of 175 °C.

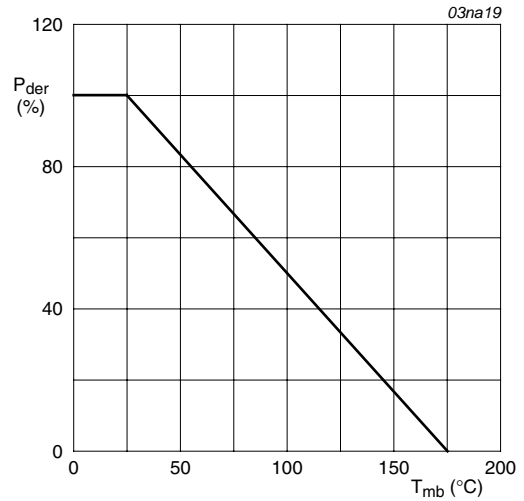
[6] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[7] Refer to application note AN10273 for further information.



$V_{GS} \geq 5 V$
 (1) Capped at 75 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100 \%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature

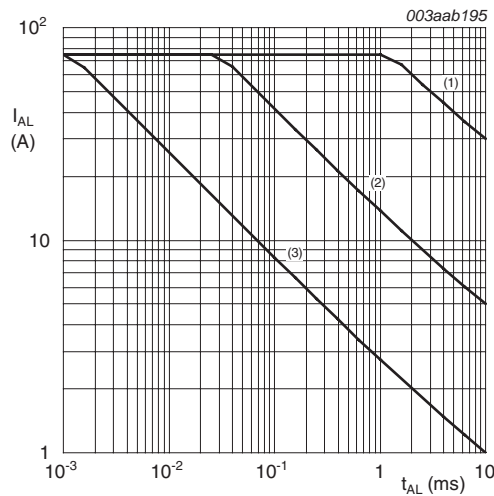


Fig 3. Single shot and repetitive avalanche rating; avalanche current as a function of avalanche time

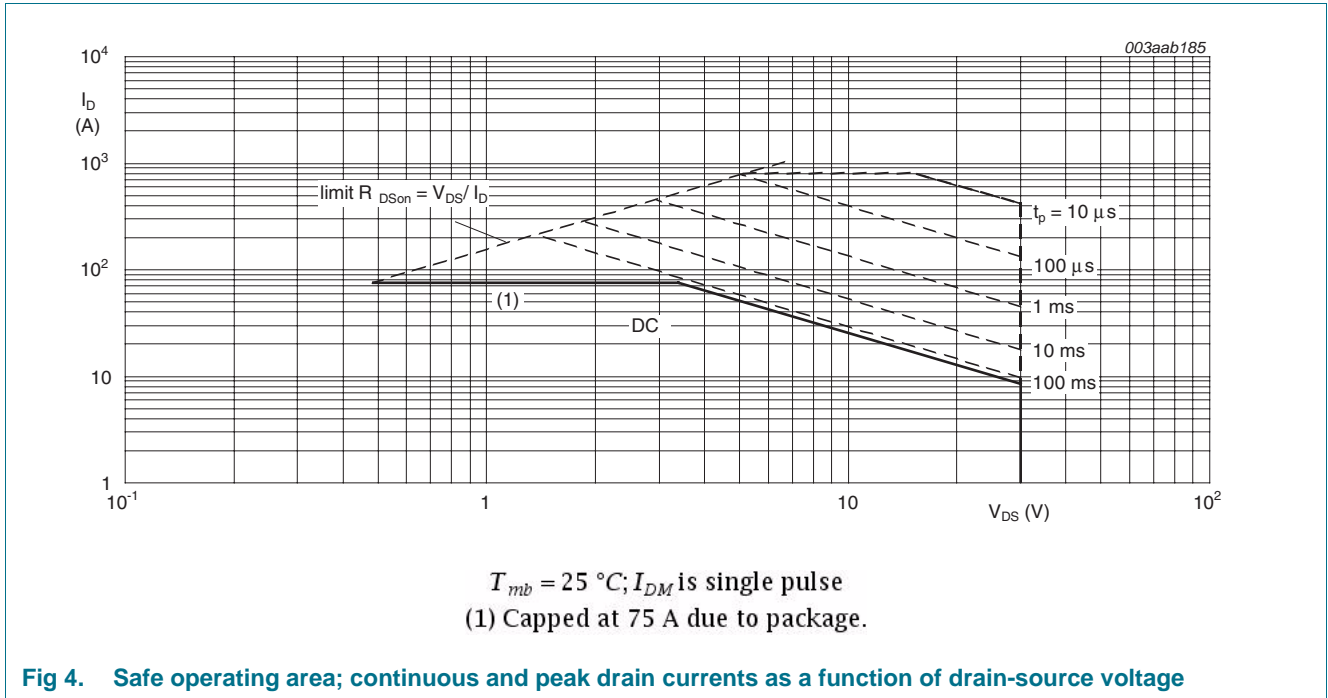


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.59	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint; vertical in still air	-	50	-	K/W

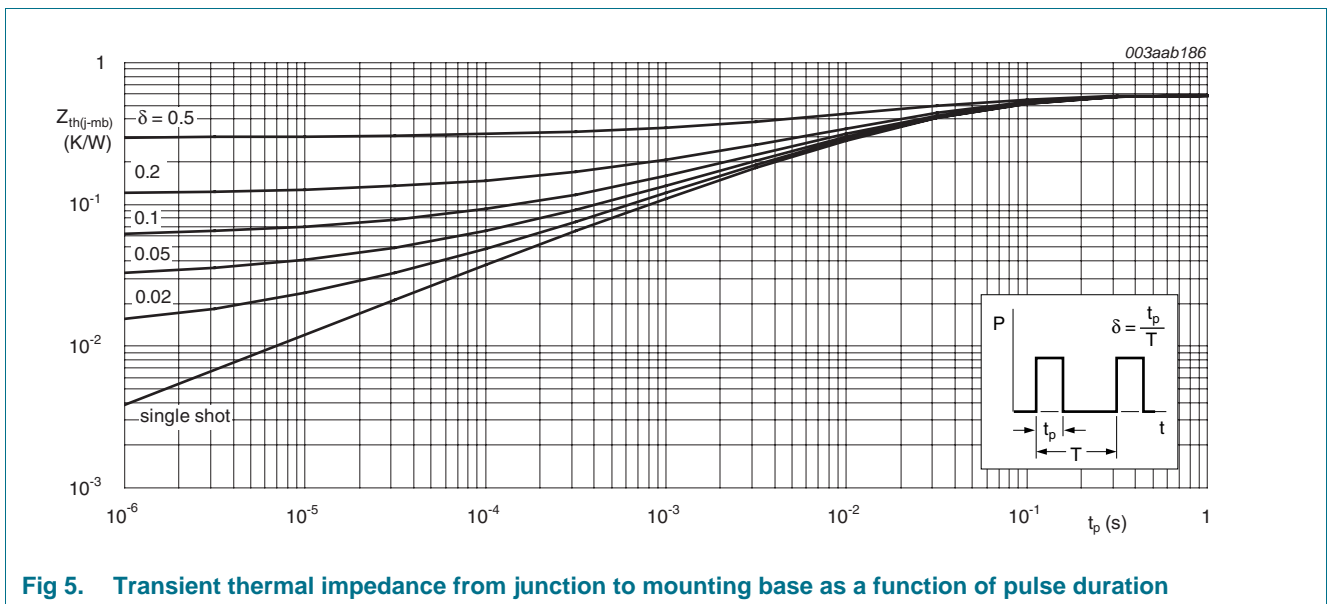
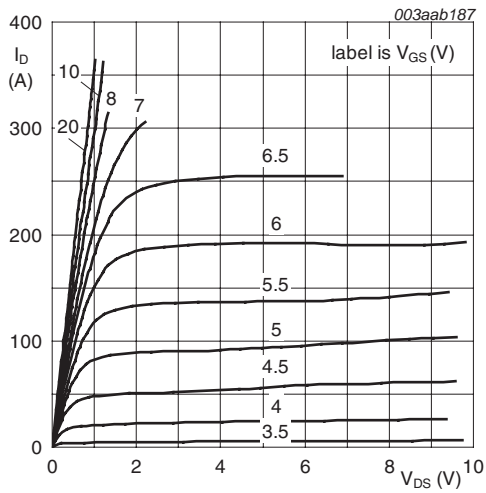


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

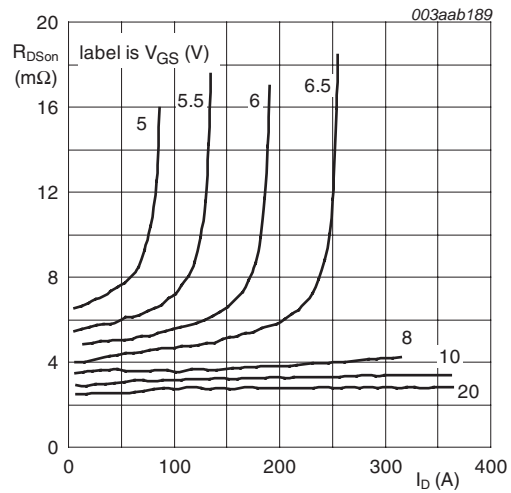
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$; see Figure 10 ; see Figure 11	2	3	4	V
V_{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$; see Figure 10 ; see Figure 11	-	-	4.4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C$; see Figure 10 ; see Figure 11	1	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.05	10	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_j = 175 \text{ }^\circ C$; see Figure 12 ; see Figure 13	-	-	6.5	m Ω
		$V_{GS} = 10 V; I_D = 25 A; T_j = 25 \text{ }^\circ C$; see Figure 12 ; see Figure 13	-	2.9	3.4	m Ω
I_{DSS}	drain leakage current	$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	μA
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 A; V_{DS} = 24 V; V_{GS} = 10 V$; see Figure 14	-	75	-	nC
Q_{GS}	gate-source charge		-	19	-	nC
Q_{GD}	gate-drain charge		-	23	-	nC
C_{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 \text{ MHz}$;	-	3713	4951	pF
C_{oss}	output capacitance	$T_j = 25 \text{ }^\circ C$; see Figure 15	-	1249	1499	pF
C_{rss}	reverse transfer capacitance		-	460	630	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 V; R_L = 1.2 \text{ } \Omega; V_{GS} = 10 V$;	-	32	-	ns
t_r	rise time	$R_{G(ext)} = 10 \text{ } \Omega$	-	64	-	ns
$t_{d(off)}$	turn-off delay time		-	89	-	ns
t_f	fall time		-	71	-	ns
L_D	internal drain inductance	from contact screw on mounting base to centre of die	-	3.5	-	nH
		from upper edge of drain mounting base to centre of die	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die	-	4.5	-	nH
L_S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$; see Figure 16	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 20 A; dI_S/dt = -100 \text{ A}/\mu s; V_{GS} = 0 V$;	-	70	-	ns
Q_r	recovered charge	$V_{DS} = 30 V$	-	58	-	nC



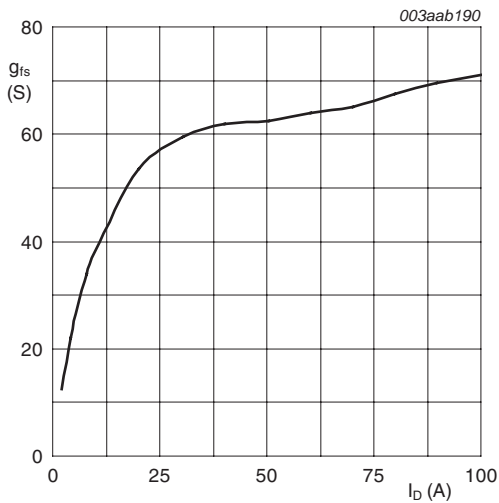
$T_j = 25\text{ }^\circ\text{C}$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



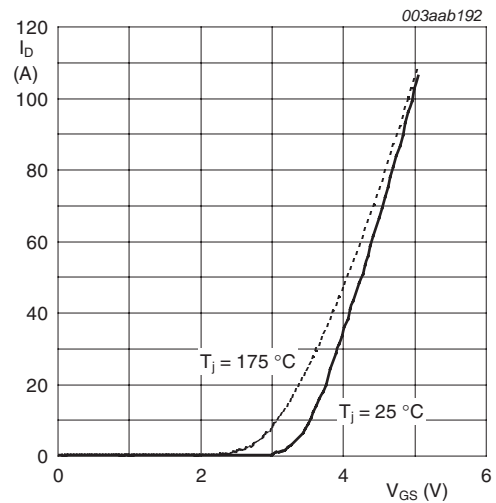
$T_j = 25\text{ }^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values



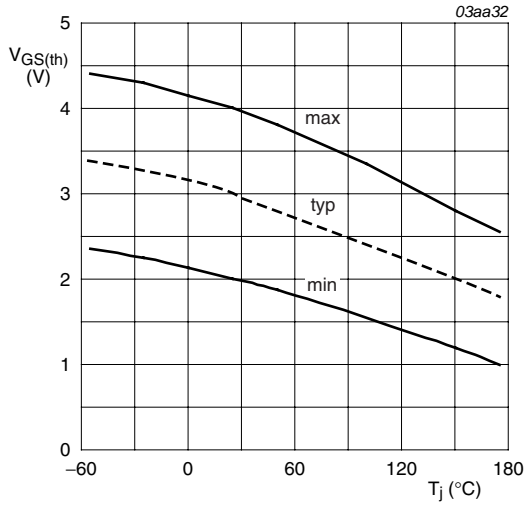
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 25\text{ V}$

Fig 8. Forward transconductance as a function of drain current; typical values



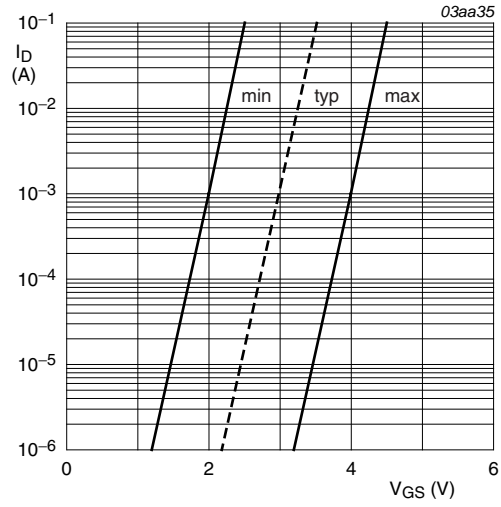
$V_{DS} = 25\text{ V}$

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



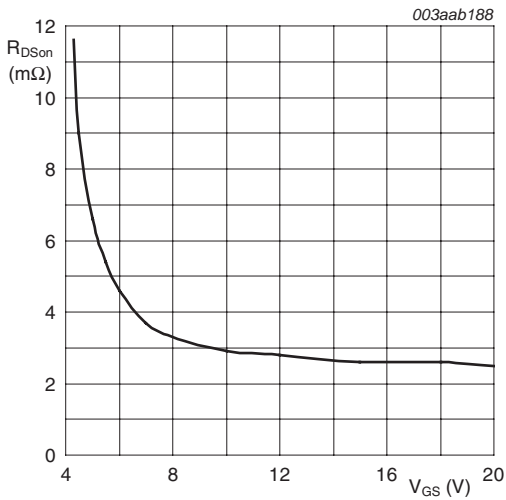
$$I_D = 1\text{mA}; V_{DS} = V_{GS}$$

Fig 10. Gate-source threshold voltage as a function of junction temperature



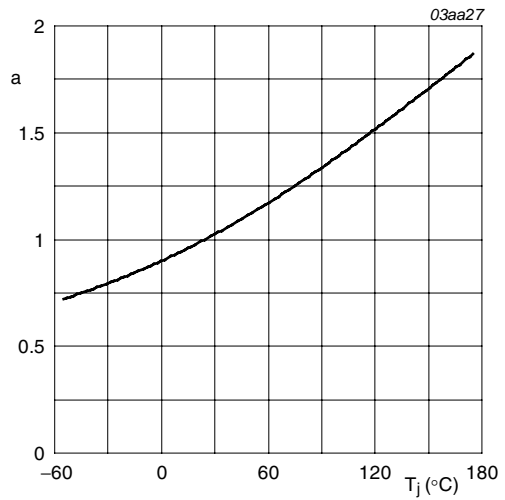
$$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{V}$$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



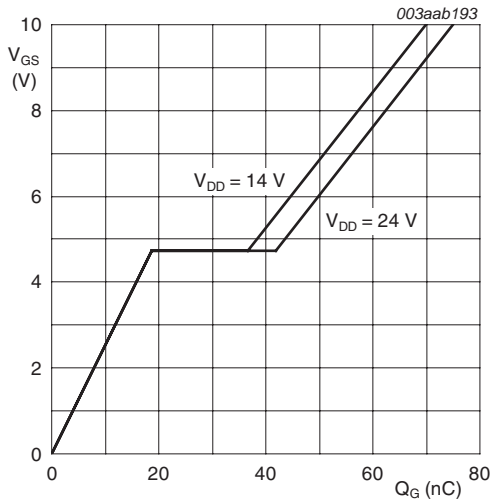
$$T_j = 25\text{ }^\circ\text{C}; I_D = 10\text{ A}$$

Fig 12. Drain-source on-state resistance as a function of gate-source voltage; typical values



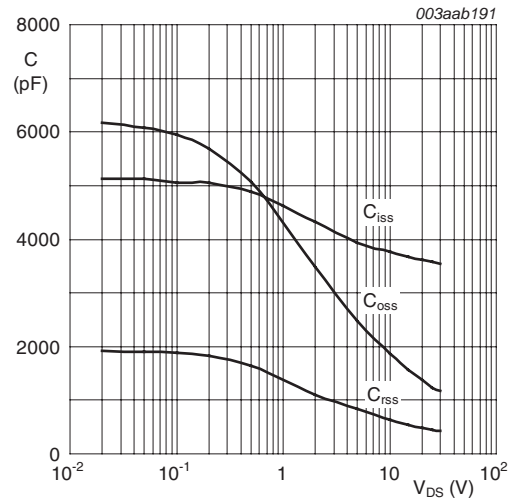
$$a = \frac{R_{DSon}}{R_{DSon@25^\circ\text{C}}}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature



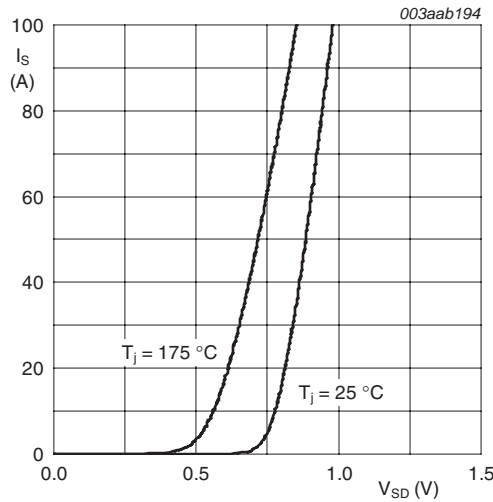
$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$

Fig 14. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$V_{GS} = 0\text{ V}$

Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404



Fig 17. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK763R4-30B v.2	20110421	Product data sheet	-	BUK75_763R4-30B_1
Modifications:	<ul style="list-style-type: none">• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.• Legal texts have been adapted to the new company name where appropriate.• Type number BUK763R4-30B separated from data sheet BUK75_763R4-30B_1.			
BUK75_763R4-30B_1	20060105	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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